

General Description

The BSC050N10NS5 use advanced SGT MOSFET

technology to provide low RDS(ON), low gate charge,

fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable.

General Features

V_{DS} =85V I_D =100A

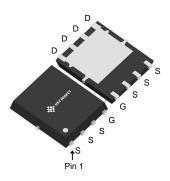
 $R_{DS(ON)} < 5.6 m\Omega @ V_{GS} = 10V$

Applications

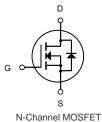
Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications



DFN5X6-8L (DFN-8(5.2x5.9))



N-Charmer WOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BSC050N10NS5	DFN5X6-8L(DFN-8(5.2x5.9))	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	85	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	100	Α
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	63.3	Α
IDM	Pulsed Drain Current ²	400	Α
EAS	Single Pulse Avalanche Energy ³	273.8	mJ
P _D @T _C =25°C	Total Power Dissipation ⁴	107.8	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Reuc	Thermal Resistance from Junction-to-Ambient ³	1.16	°C/W
R _θ JA	Thermal Resistance Junction-Ambient ¹	60	°C/W

N-SGT Enhancement Mode MOSFET

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics								
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	85	-	-	V	
Gate-body Leakage current		Igss	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain	TJ=25°C	I _{DSS}	V _{DS} = 85V, V _{GS} = 0V	-	-	1	- μΑ	
Current	T _J =100°C			-	-	100		
Gate-Threshold Voltage		$V_{GS(th)}$	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V	
Drain-Source on-Resistance⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	4.3	5.6	mΩ	
Forward Transconductance ⁴		G fs	V _{DS} = 5V, I _D =20A	-	57.8	-	S	
Dynamic Characteristic	s ⁵			•				
Input Capacitance		C _{iss}		-	4645	-		
Output Capacitance		Coss	V _{DS} = 40V, V _{GS} =0V, f =1MHz	-	673	-	pF	
Reverse Transfer Capacitance		Crss		-	41	-		
Gate Resistance		Rg	f=1MHz	-	2.0	-	Ω	
Switching Characteristi	Switching Characteristics ⁵							
Total Gate Charge		Qg		-	61.3	-	nC	
Gate-Source Charge		Qgs	$V_{GS} = 10V, V_{DS} = 40V,$ $I_{D} = 20A$	-	21	-		
Gate-Drain Charge		Q _{gd}		-	11	-		
Turn-on Delay Time	Turn-on Delay Time			-	16.5	-	. ns	
Rise Time		t _r	$V_{GS} = 10V, V_{DD} = 40V,$ $R_{G} = 3\Omega, I_{D} = 20A$	-	51.8	_		
Turn-off Delay Time		t _{d(off)}		-	37.1	-		
Fall Time		t _f		-	8.2	-		
Body Diode Reverse Recovery Time		t _{rr}		-	69	-	ns	
Body Diode Reverse Recovery Charge		Qrr	- I _F =20A, di/dt = 100A/μS	-	141	-	nC	
Drain-Source Body Diode Characteristics								
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V	
Continuous Source Current T _C =25°C		ls	-	-	-	100	Α	

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature $TJ(MAX)=150^{\circ}C$
- 2. The EAS data shows Max. rating . The test condition is V_{DD} =50V, V_{GS} =10V, L=0.4mH, I_{AS} =37A
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
- 5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

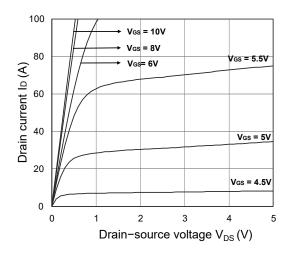


Figure 1. Output Characteristics

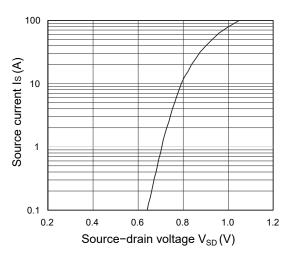


Figure 3. Forward Characteristics of Reverse

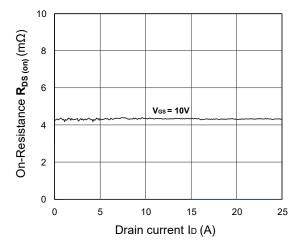


Figure 5. $R_{DS(ON)}$ vs. I_D

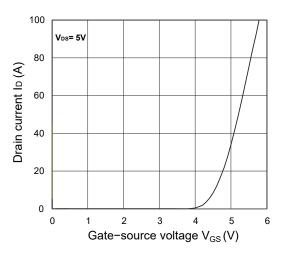


Figure 2. Transfer Characteristics

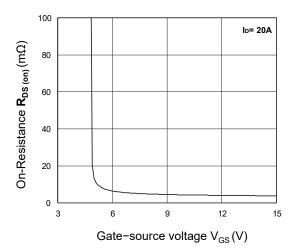


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

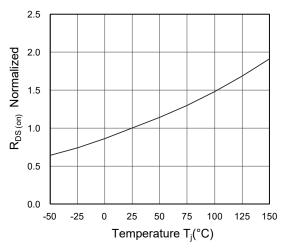
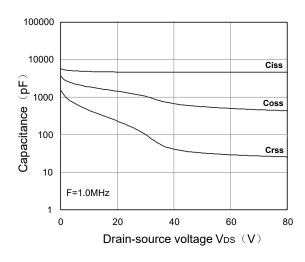


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature



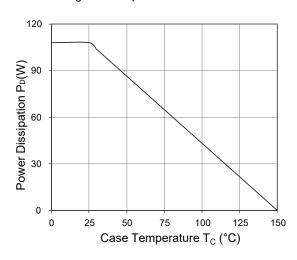
10 V_{os} = 40V l_{o= 20A}

8 l_{o= 20A}

2 0 0 20 40 60 80 O_g-Toal Gate Charge (nC)

Figure 7. Capacitance Characteristics

Figure 8. Gate Charge Characteristics



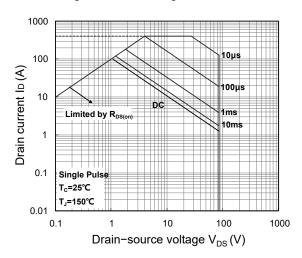


Figure 9. Power Dissipation

Figure 10. Safe Operating Area

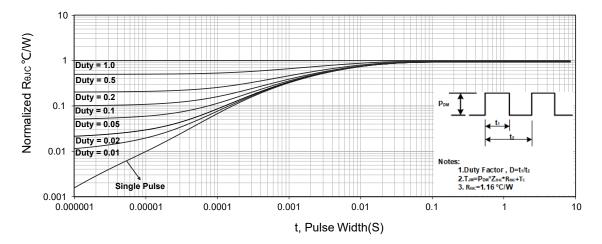
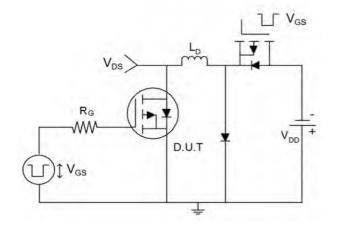
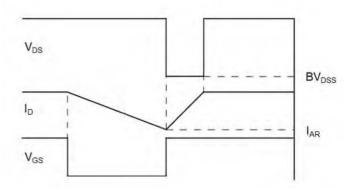


Figure 11. Normalized Maximum Transient Thermal Impedance

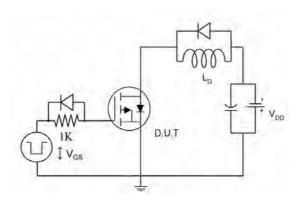


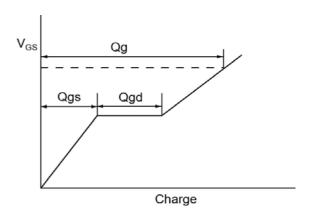
1) E_{AS} Test Circuits



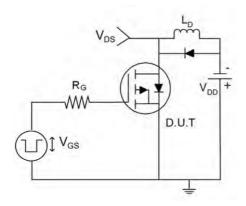


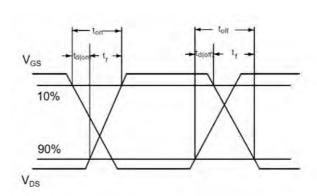
2) Gate Charge Test Circuit





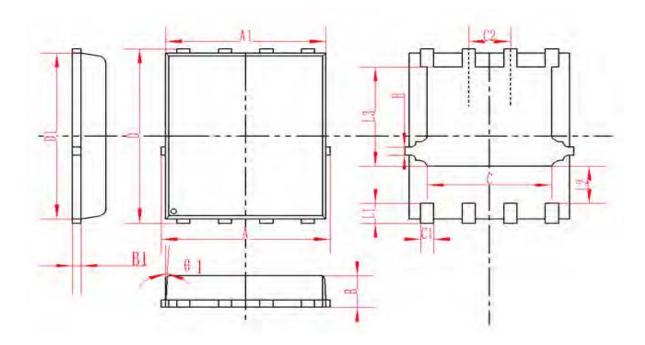
3) Switch Time Test Circuit







DFN5X6-8L(DFN-8(5.2x5.9)) Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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